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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

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Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	147456
Number of I/O	97
Number of Gates	100000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	144-LBGA
Supplier Device Package	144-FPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3p1000l-1fgg144i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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Note: Flash*Freeze technology only applies to IGLOO and ProASIC3L families.





Note: * AGLP030 does not contain a PLL or support AES security.

Figure 1-6 • IGLOO PLUS Device Architecture Overview with Four I/O Banks

ProASIC3L FPGA Fabric User's Guide

Date	Changes					
v2.1 (October 2008)	The title changed from "Flash*Freeze Technology and Low Power Modes in IGLOO, IGLOO PLUS, and ProASIC3L Devices" to Actel's Flash*Freeze Technology and Low Power Modes."					
	The "Flash Families Support the Flash*Freeze Feature" section was updated.					
	Significant changes were made to this document to support Libero IDE v8.4 and later functionality. RT ProASIC3 device support information is new. In addition to the other major changes, the following tables and figures were updated or are new:					
	Figure 2-3 • Flash*Freeze Mode Type 2 – Controlled by Flash*Freeze Pin and Internal Logic (LSICC signal) – updated	27				
	Figure 2-5 • Narrow Clock Pulses During Flash*Freeze Entrance and Exit – new	00				
	Figure 2-10 • Flash*Freeze Management IP Block Diagram – new	30				
	Table 2-11 • FSM State Diagram – New	37 38				
	2)—I/O Pad State – updated	29				
	Please review the entire document carefully.					
v1.3 (June 2008)	The family description for ProASIC3L in Table 2-1 • Flash-Based FPGAs was updated to include 1.5 V.	22				
v1.2 (March 2008)	The part number for this document was changed from 51700094-003-1 to 51700094-004-2.					
	The title of the document was changed to "Flash*Freeze Technology and Low Power Modes in IGLOO, IGLOO PLUS, and ProASIC3L Devices."	N/A				
	The "Flash*Freeze Technology and Low Power Modes" section was updated to remove the parenthetical phrase, "from 25 μ W," in the second paragraph. The following sentence was added to the third paragraph: "IGLOO PLUS has an additional feature when operating in Flash*Freeze mode, allowing it to retain I/O states as well as SRAM and register states."	21				
	The "Power Conservation Techniques" section was updated to add V_{JTAG} to the parenthetical list of power supplies that should be tied to the ground plane if unused. Additional information was added regarding how the software configures unused I/Os.	2-1				
	Table 2-1 • Flash-Based FPGAs and the accompanying text was updated to include the IGLOO PLUS family. The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	22				
	The "Flash*Freeze Mode" section was revised to include that I/O states are preserved in Flash*Freeze mode for IGLOO PLUS devices. The last sentence in the second paragraph was changed to, "If the FF pin is not used, it can be used as a regular I/O." The following sentence was added for Flash*Freeze mode type 2: "Exiting the mode is controlled by either the FF pin OR the user-defined LSICC signal."	24				
	The "Flash*Freeze Type 1: Control by Dedicated Flash*Freeze Pin" section was revised to change instructions for implementing this mode, including instructions for implementation with Libero IDE v8.3.	24				
	Figure 2-1 • Flash*Freeze Mode Type 1 – Controlled by the Flash*Freeze Pin was updated.	25				
	The "Flash*Freeze Type 2: Control by Dedicated Flash*Freeze Pin and Internal Logic" section was renamed from "Type 2 Software Implementation."	26				
	The "Type 2 Software Implementation for Libero IDE v8.3" section is new.	2-6				

Flash*Freeze Technology and Low Power Modes

Date	Changes				
v1.2 (continued)	Figure 2-3 • Flash*Freeze Mode Type 2 – Controlled by Flash*Freeze Pin and Internal Logic (LSICC signal) was updated.	27			
	Figure 2-4 • Flash*Freeze Mode Type 2 – Timing Diagram was revised to show deasserting LSICC after the device has exited Flash*Freeze mode.				
	The "IGLOO nano and IGLOO PLUS I/O State in Flash*Freeze Mode" section was added to include information for IGLOO PLUS devices. Table 2-6 • IGLOO nano and IGLOO PLUS Flash*Freeze Mode (type 1 and type 2)—I/O Pad State is new.	28, 29			
	The "During Flash*Freeze Mode" section was revised to include a new bullet pertaining to output behavior for IGLOO PLUS. The bullet on JTAG operation was revised to provide more detail.	31			
	Figure 2-6 • Controlling Power-On/-Off State Using Microprocessor and Power FET and Figure 2-7 • Controlling Power-On/-Off State Using Microprocessor and Voltage Regulator were updated to include IGLOO PLUS.	33, 33			
	The first sentence of the "Shutdown Mode" section was updated to list the devices for which it is supported.	32			
	The first paragraph of the "Power-Up/-Down Behavior" section was revised. The second sentence was changed to, "The I/Os remain tristated until the last voltage supply (V_{CC} or V_{CCI}) is powered to its activation level." The word "activation" replaced the word "functional." The sentence, "During power-down, device I/Os become tristated once the first power supply (V_{CC} or V_{CCI}) drops below its deactivation voltage level" was revised. The word "deactivation" replaced the word "functional."	33			
	The "Prototyping for IGLOO and ProASIC3L Devices Using ProASIC3" section was revised to state that prototyping in ProASIC3 does not apply for the IGLOO PLUS family.	2-21			
	Table 2-8 • Prototyping/Migration Solutions, Table 2-9 • Device Migration—IGLOO Supported Packages in ProASIC3 Devices, and Table 2-10 • Device Migration— ProASIC3L Supported Packages in ProASIC3 Devices were updated with a table note stating that device migration is not supported for IGLOO PLUS devices.	2-21, 2-23			
	The text following Table 2-10 • Device Migration—ProASIC3L Supported Packages in ProASIC3 Devices was moved to a new section: the "Flash*Freeze Design Guide" section.	34			
v1.1 (February 2008)	Table 2-1 • Flash-Based FPGAs was updated to remove the ProASIC3, ProASIC3E, and Automotive ProASIC3 families, which were incorrectly included.	22			
v1.0 (January 2008)	Detailed descriptions of low power modes are described in the advanced datasheets. This application note was updated to describe how to use the features in an IGLOO/e application.				
	Figure 2-1 • Flash*Freeze Mode Type 1 – Controlled by the Flash*Freeze Pin was updated.				
	Figure 2-2 • Flash*Freeze Mode Type 1 – Timing Diagram is new.	25			
	Steps 4 and 5 are new in the "Flash*Freeze Type 2: Control by Dedicated Flash*Freeze Pin and Internal Logic" section.	26			

standard for CLKBUF is LVTTL in the current Microsemi Libero $^{\ensuremath{\mathbb{R}}}$ System-on-Chip (SoC) and Designer software.

Name	Description			
CLKBUF_LVCMOS5	LVCMOS clock buffer with 5.0 V CMOS voltage level			
CLKBUF_LVCMOS33	LVCMOS clock buffer with 3.3 V CMOS voltage level			
CLKBUF_LVCMOS25	LVCMOS clock buffer with 2.5 V CMOS voltage level ¹			
CLKBUF_LVCMOS18	LVCMOS clock buffer with 1.8 V CMOS voltage level			
CLKBUF_LVCMOS15	LVCMOS clock buffer with 1.5 V CMOS voltage level			
CLKBUF_LVCMOS12	LVCMOS clock buffer with 1.2 V CMOS voltage level			
CLKBUF_PCI	PCI clock buffer			
CLKBUF_PCIX	PCIX clock buffer			
CLKBUF_GTL25	GTL clock buffer with 2.5 V CMOS voltage level ¹			
CLKBUF_GTL33	GTL clock buffer with 3.3 V CMOS voltage level ¹			
CLKBUF_GTLP25	GTL+ clock buffer with 2.5 V CMOS voltage level ¹			
CLKBUF_GTLP33	GTL+ clock buffer with 3.3 V CMOS voltage level ¹			
CLKBUF_HSTL_I	HSTL Class I clock buffer ¹			
CLKBUF_HSTL_II	HSTL Class II clock buffer ¹			
CLKBUF_SSTL2_I	SSTL2 Class I clock buffer ¹			
CLKBUF_SSTL2_II	SSTL2 Class II clock buffer ¹			
CLKBUF_SSTL3_I	SSTL3 Class I clock buffer ¹			
CLKBUF_SSTL3_II	SSTL3 Class II clock buffer ¹			

Table 3-9 • I/O Standards within CLKBUF

Notes:

- 1. Supported in only the IGLOOe, ProASIC3E, AFS600, and AFS1500 devices
- 2. By default, the CLKBUF macro uses the 3.3 V LVTTL I/O technology.

The current synthesis tool libraries only infer the CLKBUF or CLKINT macros in the netlist. All other global macros must be instantiated manually into your HDL code. The following is an example of CLKBUF LVCMOS25 global macro instantiations that you can copy and paste into your code:

VHDL

```
component clkbuf_lvcmos25
  port (pad : in std_logic; y : out std_logic);
end component
```

begin

```
-- concurrent statements
u2 : clkbuf_lvcmos25 port map (pad => ext_clk, y => int_clk);
end
```

Verilog

module design (_____);

input ____; output ____;

clkbuf_lvcmos25 u2 (.y(int_clk), .pad(ext_clk);

endmodule



Global Resources in Low Power Flash Devices

External I/O or Local signal as Clock Source

External I/O refers to regular I/O pins are labeled with the I/O convention IOuxwByVz. You can allow the external I/O or internal signal to access the global. To allow the external I/O or internal signal to access the global network, you need to instantiate the CLKINT macro. Refer to Figure 3-4 on page 51 for an example illustration of the connections. Instead of using CLKINT, you can also use PDC to promote signals from external I/O or internal signal to the global network. However, it may cause layout issues because of synthesis logic replication. Refer to the "Global Promotion and Demotion Using PDC" section on page 67 for details.



Figure 3-14 • CLKINT Macro

Using Global Macros in Synplicity

The Synplify[®] synthesis tool automatically inserts global buffers for nets with high fanout during synthesis. By default, Synplicity[®] puts six global macros (CLKBUF or CLKINT) in the netlist, including any global instantiation or PLL macro. Synplify always honors your global macro instantiation. If you have a PLL (only primary output is used) in the design, Synplify adds five more global buffers in the netlist. Synplify uses the following global counting rule to add global macros in the netlist:

- 1. CLKBUF: 1 global buffer
- 2. CLKINT: 1 global buffer
- 3. CLKDLY: 1 global buffer
- 4. PLL: 1 to 3 global buffers
 - GLA, GLB, GLC, YB, and YC are counted as 1 buffer.
 - GLB or YB is used or both are counted as 1 buffer.
 - GLC or YC is used or both are counted as 1 buffer.

Global Resources in Low Power Flash Devices

Date	Changes				
v1.1 (March 2008)	The "Global Architecture" section was updated to include the IGLOO PLUS family. The bullet was revised to include that the west CCC does not contain a PLL core in 15 k and 30 k devices. Instances of "A3P030 and AGL030 devices" were replaced with "15 k and 30 k gate devices."				
v1.1 (continued)	Table 3-1 • Flash-Based FPGAs and the accompanying text was updated to include the IGLOO PLUS family. The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	48			
	The "VersaNet Global Network Distribution" section, "Spine Architecture" section, the note in Figure 3-1 • Overview of VersaNet Global Network and Device Architecture, and the note in Figure 3-3 • Simplified VersaNet Global Network (60 k gates and above) were updated to include mention of 15 k gate devices.	49, 50			
	Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices was updated to add the A3P015 device, and to revise the values for clock trees, globals/spines per tree, and globals/spines per device for the A3P030 and AGL030 devices.				
	Table 3-5 • Globals/Spines/Rows for IGLOO PLUS Devices is new.				
	CLKBUF_LVCMOS12 was added to Table 3-9 • I/O Standards within CLKBUF.	63			
	The "User's Guides" section was updated to include the three different I/O Structures chapters for ProASIC3 and IGLOO device families.	74			
v1.0 (January 2008)	Figure 3-3 • Simplified VersaNet Global Network (60 k gates and above) was updated.	50			
	The "Naming of Global I/Os" section was updated.	51			
	The "Using Global Macros in Synplicity" section was updated.	66			
	The "Global Promotion and Demotion Using PDC" section was updated.				
	The "Designer Flow for Global Assignment" section was updated.				
	The "Simple Design Example" section was updated.				
51900087-0/1.05Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices was updated.					



Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

Primary Clock Output Delay from CLKA -3.020 Secondary1 Clock frequency 40.000 Secondary1 Clock Phase Shift 0.000 Secondary1 Clock Global Output Delay from CLKA 2.515

Next, perform simulation in Model*Sim* to verify the correct delays. Figure 4-30 shows the simulation results. The delay values match those reported in the SmartGen PLL Wizard.



Figure 4-30 • Model Sim Simulation Results

The timing can also be analyzed using SmartTime in Designer. The user should import the synthesized netlist to Designer, perform Compile and Layout, and then invoke SmartTime. Go to **Tools** > **Options** and change the maximum delay operating conditions to **Typical Case**. Then expand the Clock-to-Out paths of GLA and GLB and the individual components of the path delays are shown. The path of GLA is shown in Figure 4-31 on page 123 displaying the same delay value.

Figure 4-31 • Static Timing Analysis Using SmartTime

Place-and-Route Stage Considerations

Several considerations must be noted to properly place the CCC macros for layout. For CCCs with clock inputs configured with the Hardwired I/O–Driven option:

- PLL macros must have the clock input pad coming from one of the GmA* locations.
- CLKDLY macros must have the clock input pad coming from one of the Global I/Os.

If a PLL with a Hardwired I/O input is used at a CCC location and a Hardwired I/O–Driven CLKDLY macro is used at the same CCC location, the clock input of the CLKDLY macro must be chosen from one of the GmB* or GmC* pin locations. If the PLL is not used or is an External I/O–Driven or Core Logic–Driven PLL, the clock input of the CLKDLY macro can be sourced from the GmA*, GmB*, or GmC* pin locations.

For CCCs with clock inputs configured with the External I/O–Driven option, the clock input pad can be assigned to any regular I/O location (IO******* pins). Note that since global I/O pins can also be used as regular I/Os, regardless of CCC function (CLKDLY or PLL), clock inputs can also be placed in any of these I/O locations.

By default, the Designer layout engine will place global nets in the design at one of the six chip globals. When the number of globals in the design is greater than six, the Designer layout engine will automatically assign additional globals to the quadrant global networks of the low power flash devices. If the user wishes to decide which global signals should be assigned to chip globals (six available) and which to the quadrant globals (three per quadrant for a total of 12 available), the assignment can be achieved with PinEditor, ChipPlanner, or by importing a placement constraint file. Layout will fail if the



Figure 5-7 • Accessing FlashROM Using FPGA Core



Figure 5-8 • Accessing FlashROM Using JTAG Port

SRAM and FIFO Memories in Microsemi's Low Power Flash Devices



Note: For timing diagrams of the RAM signals, refer to the appropriate family datasheet.

Figure 6-5 • 512X18 Two-Port RAM Block Diagram

Signal Descriptions for RAM512X18

RAM512X18 has slightly different behavior from RAM4K9, as it has dedicated read and write ports.

WW and RW

These signals enable the RAM to be configured in one of the two allowable aspect ratios (Table 6-5).

WW[1:0]	RW[1:0]	D×W
01	01	512×9
10	10	256×18
00, 11	00, 11	Reserved

WD and RD

These are the input and output data signals, and they are 18 bits wide. When a 512×9 aspect ratio is used for write, WD[17:9] are unused and must be grounded. If this aspect ratio is used for read, RD[17:9] are undefined.

WADDR and RADDR

These are read and write addresses, and they are nine bits wide. When the 256×18 aspect ratio is used for write or read, WADDR[8] and RADDR[8] are unused and must be grounded.

WCLK and RCLK

These signals are the write and read clocks, respectively. They can be clocked on the rising or falling edge of WCLK and RCLK.

WEN and REN

These signals are the write and read enables, respectively. They are both active-low by default. These signals can be configured as active-high.

RESET

This active-low signal resets the control logic, forces the output hold state registers to zero, disables reads and writes from the SRAM block, and clears the data hold registers when asserted. It does not reset the contents of the memory array.

While the RESET signal is active, read and write operations are disabled. As with any asynchronous reset signal, care must be taken not to assert it too close to the edges of active read and write clocks.

PIPE

This signal is used to specify pipelined read on the output. A LOW on PIPE indicates a nonpipelined read, and the data appears on the output in the same clock cycle. A HIGH indicates a pipelined read, and data appears on the output in the next clock cycle.

SRAM Usage

The following descriptions refer to the usage of both RAM4K9 and RAM512X18.

Clocking

The dual-port SRAM blocks are only clocked on the rising edge. SmartGen allows falling-edge-triggered clocks by adding inverters to the netlist, hence achieving dual-port SRAM blocks that are clocked on either edge (rising or falling). For dual-port SRAM, each port can be clocked on either edge and by separate clocks by port. Note that for Automotive ProASIC3, the same clock, with an inversion between the two clock pins of the macro, should be used in design to prevent errors during compile.

Low power flash devices support inversion (bubble-pushing) throughout the FPGA architecture, including the clock input to the SRAM modules. Inversions added to the SRAM clock pin on the design schematic or in the HDL code will be automatically accounted for during design compile without incurring additional delay in the clock path.

The two-port SRAM can be clocked on the rising or falling edge of WCLK and RCLK.

If negative-edge RAM and FIFO clocking is selected for memory macros, clock edge inversion management (bubble-pushing) is automatically used within the development tools, without performance penalty.

Modes of Operation

There are two read modes and one write mode:

- Read Nonpipelined (synchronous—1 clock edge): In the standard read mode, new data is driven
 onto the RD bus in the same clock cycle following RA and REN valid. The read address is
 registered on the read port clock active edge, and data appears at RD after the RAM access time.
 Setting PIPE to OFF enables this mode.
- Read Pipelined (synchronous—2 clock edges): The pipelined mode incurs an additional clock delay from address to data but enables operation at a much higher frequency. The read address is registered on the read port active clock edge, and the read data is registered and appears at RD after the second read clock edge. Setting PIPE to ON enables this mode.
- Write (synchronous—1 clock edge): On the write clock active edge, the write data is written into the SRAM at the write address when WEN is HIGH. The setup times of the write address, write enables, and write data are minimal with respect to the write clock.

RAM Initialization

Each SRAM block can be individually initialized on power-up by means of the JTAG port using the UJTAG mechanism. The shift register for a target block can be selected and loaded with the proper bit configuration to enable serial loading. The 4,608 bits of data can be loaded in a single operation.

FIFO Features

The FIFO4KX18 macro is created by merging the RAM block with dedicated FIFO logic (Figure 6-6 on page 158). Since the FIFO logic can only be used in conjunction with the memory block, there is no separate FIFO controller macro. As with the RAM blocks, the FIFO4KX18 nomenclature does not refer to a possible aspect ratio, but rather to the deepest possible data depth and the widest possible data width. FIFO4KX18 can be configured into the following aspect ratios: 4,096×1, 2,048×2, 1,024×4, 512×9, and 256×18. In addition to being fully synchronous, the FIFO4KX18 also has the following features:

- Four FIFO flags: Empty, Full, Almost-Empty, and Almost-Full
- Empty flag is synchronized to the read clock
- Full flag is synchronized to the write clock
- Both Almost-Empty and Almost-Full flags have programmable thresholds
- · Active-low asynchronous reset
- Active-low block enable
- Active-low write enable
- Active-high read enable
- Ability to configure the FIFO to either stop counting after the empty or full states are reached or to allow the FIFO counters to continue

Table 6-10 • RAM and FIFO Memory Block Consumption

		Depth										
			2	56	512	1,024	2,048	4,096	8,192	16,384	32,768	65,536
			Two-Port	Dual-Port	Dual-Port	Dual-Port	Dual-Port	Dual-Port	Dual-Port	Dual-Port	Dual-Port	Dual-Port
	1	Number Block	1	1	1	1	1	1	2	4	8	16 × 1
		Configuration	Any	Any	Any	1,024 × 4	2,048 × 2	4,096 × 1	2 × (4,096 × 1) Cascade Deep	4 × (4,096 × 1) Cascade Deep	8 × (4,096 × 1) Cascade Deep	16 × (4,096 × 1) Cascade Deep
	2	Number Block	1	1	1	1	1	2	4	8	16	32
		Configuration	Any	Any	Any	1,024×4	2,048 × 2	2 × (4,096 × 1) Cascaded Wide	4 × (4,096 × 1) Cascaded 2 Deep and 2 Wide	8 × (4,096 × 1) Cascaded 4 Deep and 2 Wide	16 × (4,096 × 1) Cascaded 8 Deep and 2 Wide	32 × (4,096 × 1) Cascaded 16 Deep and 2 Wide
	4	Number Block	1	1	1	1	2	4	8	16	32	64
		Configuration	Any	Any	Any	1,024 × 4	2 × (2,048 × 2) Cascaded Wide	4 × (4,096 × 1) Cascaded Wide	4 × (4,096 × 1) Cascaded 2 Deep and 4 Wide	16 × (4,096 × 1) Cascaded 4 Deep and 4 Wide	32 × (4,096 × 1) Cascaded 8 Deep and 4 Wide	64 × (4,096 × 1) Cascaded 16 Deep and 4 Wide
	8	Number Block	1	1	1	2	4	8	16	32	64	
		Configuration	Any	Any	Any	2 × (1,024 × 4) Cascaded Wide	4 × (2,048 × 2) Cascaded Wide	8 × (4,096 × 1) Cascaded Wide	16 × (4,096 × 1) Cascaded 2 Deep and 8 Wide	32 × (4,096 × 1) Cascaded 4 Deep and 8 Wide	64 × (4,096 × 1) Cascaded 8 Deep and 8 Wide	
	9	Number Block	1	1	1	2	4	8	16	32		
Width		Configuration	Any	Any	Any	2 × (512 × 9) Cascaded Deep	4 × (512 × 9) Cascaded Deep	8 × (512 × 9) Cascaded Deep	16 × (512 × 9) Cascaded Deep	32 × (512 × 9) Cascaded Deep		
	16	Number Block	1	1	1	4	8	16	32	64		
		Configuration	256 × 18	256 × 18	256 × 18	4 × (1,024 × 4) Cascaded Wide	8 × (2,048 × 2) Cascaded Wide	16 × (4,096 × 1) Cascaded Wide	32 × (4,096 × 1) Cascaded 2 Deep and 16 Wide	32 × (4,096 × 1) Cascaded 4 Deep and 16 Wide		
	18	Number Block	1	2	2	4	8	18	32			
		Configuration	256 × 8	2 × (512 × 9) Cascaded Wide	2 × (512 × 9) Cascaded Wide	4 × (512 × 9) Cascaded 2 Deep and 2 Wide	8 × (512 × 9) Cascaded 4 Deep and 2 Wide	16 × (512 × 9) Cascaded 8 Deep and 2 Wide	16 × (512 × 9) Cascaded 16 Deep and 2 Wide			
	32	Number Block	2	4	4	8	16	32	64			
		Configuration	2 × (256 × 18) Cascaded Wide	4 × (512 × 9) Cascaded Wide	4 × (512 × 9) Cascaded Wide	8 × (1,024 × 4) Cascaded Wide	16 × (2,048 × 2) Cascaded Wide	32 × (4,096 × 1) Cascaded Wide	64 × (4,096 × 1) Cascaded 2 Deep and 32 Wide			
	36	Number Block	2	4	4	8	16	32				
		Configuration	2 × (256 × 18) Cascaded Wide	4 × (512 × 9) Cascaded Wide	4 × (512 × 9) Cascaded Wide	4 × (512 × 9) Cascaded 2 Deep and 4 Wide	16 × (512 × 9) Cascaded 4 Deep and 4 Wide	16 × (512 × 9) Cascaded 8 Deep and 4 Wide				
	64	Number Block	4	8	8	16	32	64				
		Configuration	4 × (256 × 18) Cascaded Wide	8 × (512 × 9) Cascaded Wide	8 × (512 × 9) Cascaded Wide	16 × (1,024 × 4) Cascaded Wide	32 × (2,048 × 2) Cascaded Wide	64 × (4,096 × 1) Cascaded Wide				
	72	Number Block	4	8	8	16	32					
		Configuration	4 × (256 × 18) Cascaded Wide	8 × (512 × 9) Cascaded Wide	8 × (512 × 9) Cascaded Wide	16 × (512 × 9) Cascaded Wide	16 × (512 × 9) Cascaded 4 Deep and 8 Wide					

Note: Memory configurations represented by grayed cells are not supported.

I/O Structures in IGLOO and ProASIC3 Devices

Board-Level Considerations

Low power flash devices have robust I/O features that can help in reducing board-level components. The devices offer single-chip solutions, which makes the board layout simpler and more immune to signal integrity issues. Although, in many cases, these devices resolve board-level issues, special attention should always be given to overall signal integrity. This section covers important board-level considerations to facilitate optimum device performance.

Termination

Proper termination of all signals is essential for good signal quality. Nonterminated signals, especially clock signals, can cause malfunctioning of the device.

For general termination guidelines, refer to the *Board-Level Considerations* application note for Microsemi FPGAs. Also refer to the "Pin Descriptions" chapter of the appropriate datasheet for termination requirements for specific pins.

Low power flash I/Os are equipped with on-chip pull-up/-down resistors. The user can enable these resistors by instantiating them either in the top level of the design (refer to the *IGLOO, Fusion, and ProASIC3 Macro Library Guide* for the available I/O macros with pull-up/-down) or in the I/O Attribute Editor in Designer if generic input or output buffers are instantiated in the top level. Unused I/O pins are configured as inputs with pull-up resistors.

As mentioned earlier, low power flash devices have multiple programmable drive strengths, and the user can eliminate unwanted overshoot and undershoot by adjusting the drive strengths.

Power-Up Behavior

Low power flash devices are power-up/-down friendly; i.e., no particular sequencing is required for power-up and power-down. This eliminates extra board components for power-up sequencing, such as a power-up sequencer.

During power-up, all I/Os are tristated, irrespective of I/O macro type (input buffers, output buffers, I/O buffers with weak pull-ups or weak pull-downs, etc.). Once I/Os become activated, they are set to the user-selected I/O macros. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373 for details.

Drive Strength

Low power flash devices have up to seven programmable output drive strengths. The user can select the drive strength of a particular output in the I/O Attribute Editor or can instantiate a specialized I/O macro, such as OUTBUF_S_12 (slew = low, out_drive = 12 mA).

The maximum available drive strength is 24 mA per I/O. Though no I/O should be forced to source or sink more than 24 mA indefinitely, I/Os may handle a higher amount of current (refer to the device IBIS model for maximum source/sink current) during signal transition (AC current). Every device package has its own power dissipation limit; hence, power calculation must be performed accurately to determine how much current can be tolerated per I/O within that limit.

I/O Interfacing

Low power flash devices are 5 V–input– and 5 V–output–tolerant if certain I/O standards are selected (refer to the "5 V Input and Output Tolerance" section on page 194). Along with other low-voltage I/O macros, this 5 V tolerance makes these devices suitable for many types of board component interfacing.



I/O Structures in IGLOOe and ProASIC3E Devices



Notes:

- 1. All NMOS transistors connected to the I/O pad serve as ESD protection.
- 2. See Table 8-2 on page 215 for available I/O standards.
- 3. Programmable input delay is applicable only to ProASIC3E, IGLOOe, ProASIC3EL, and RT ProASIC3 devices.

Figure 8-5 • Simplified I/O Buffer Circuitry

I/O Registers

Each I/O module contains several input, output, and enable registers. Refer to Figure 8-5 for a simplified representation of the I/O block. The number of input registers is selected by a set of switches (not shown in Figure 8-3 on page 220) between registers to implement single-ended or differential data transmission to and from the FPGA core. The Designer software sets these switches for the user. A common CLR/PRE signal is employed by all I/O registers when I/O register combining is used. Input Register 2 does not have a CLR/PRE pin, as this register is used for DDR implementation. The I/O register combining must satisfy certain rules.

Power-Up Behavior

Low power flash devices are power-up/-down friendly; i.e., no particular sequencing is required for power-up and power-down. This eliminates extra board components for power-up sequencing, such as a power-up sequencer.

During power-up, all I/Os are tristated, irrespective of I/O macro type (input buffers, output buffers, I/O buffers with weak pull-ups or weak pull-downs, etc.). Once I/Os become activated, they are set to the user-selected I/O macros. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373 for details.

Drive Strength

Low power flash devices have up to seven programmable output drive strengths. The user can select the drive strength of a particular output in the I/O Attribute Editor or can instantiate a specialized I/O macro, such as OUTBUF_S_12 (slew = low, out_drive = 12 mA).

The maximum available drive strength is 24 mA per I/O. Though no I/O should be forced to source or sink more than 24 mA indefinitely, I/Os may handle a higher amount of current (refer to the device IBIS model for maximum source/sink current) during signal transition (AC current). Every device package has its own power dissipation limit; hence, power calculation must be performed accurately to determine how much current can be tolerated per I/O within that limit.

I/O Interfacing

Low power flash devices are 5 V–input– and 5 V–output–tolerant if certain I/O standards are selected (refer to the "5 V Input and Output Tolerance" section on page 232). Along with other low-voltage I/O macros, this 5 V tolerance makes these devices suitable for many types of board component interfacing.

	(Clock	I/O			
Interface	Туре	Frequency	Туре	Signals In	Signals Out	Data I/O
GM	Src Sync	125 MHz	LVTTL	8	8	125 Mbps
ТВІ	Src Sync	125 MHz	LVTTL	10	10	125 Mbps
XSBI	Src Sync	644 MHz	LVDS	16	16	644 Mbps
XGMI	Src Sync DDR	156 MHz	HSTL1	32	32	312 Mbps
FlexBus 3	Sys Sync	104 MHz	LVTTL	≤ 32	≤ 32	≤ 104
Pos-PHY3/SPI-3	Sys Sync	104	LVTTL	8,16,32	8,16,32	\leq 104 Mbps
FlexBus 4/SPI-4.1	Src Sync	200 MHz	HSTL1	16,64	16,64	200 Mbps
Pos-PHY4/SPI-4.2	Src Sync DDR	≥ 311 MHz	LVDS	16	16	\geq 622 Mbps
SFI-4.1	Src Sync	622 MHz	LVDS	16	16	622 Mbps
CSIX L1	Sys Sync	\leq 250 MHz	HSTL1	32,64,96,128	32,64,96,128	\leq 250 Mbps
Hyper Transport	Sys Sync DDR	\leq 800 MHz	LVDS	2,4,8,16	2,4,8,16	\leq 1.6 Gbps
Rapid I/O Parallel	Sys Sync DDR	250 MHz – 1 GHz	LVDS	8,16	8,16	\leq 2 Gbps
Star Fabric	CDR		LVDS	4	4	622 Mbps

Table 8-19 • High-Level Interface Examples

Note: Sys Sync = System Synchronous Clocking, Src Sync = Source Synchronous Clocking, and CDR = Clock and Data Recovery.

- The I/O standard of technology-specific I/O macros cannot be changed in the I/O Attribute Editor (see Figure 9-6).
- The user MUST instantiate differential I/O macros (LVDS/LVPECL) in the design. This is the only way to use these standards in the design (IGLOO nano and ProASIC3 nano devices do not support differential inputs).
- To implement the DDR I/O function, the user must instantiate a DDR_REG or DDR_OUT macro. This is the only way to use a DDR macro in the design.

Figure 9-6 • Assigning a Different I/O Standard to the Generic I/O Macro

Performing Place-and-Route on the Design

The netlist created by the synthesis tool should now be imported into Designer and compiled. During Compile, the user can specify the I/O placement and attributes by importing the PDC file. The user can also specify the I/O placement and attributes using ChipPlanner and the I/O Attribute Editor under MVN.

Defining I/O Assignments in the PDC File

A PDC file is a Tcl script file specifying physical constraints. This file can be imported to and exported from Designer.

Table 9-3 shows I/O assignment constraints supported in the PDC file.

Command Action		Example	Comment					
I/O Banks Setting Constraints								
set_iobank	Sets the I/O supply voltage, V_{CCI} , and the input reference voltage, V_{REF} , for the specified I/O bank.	<pre>set_iobank bankname [-vcci vcci_voltage] [-vref vref_voltage] set_iobank Bank7 -vcci 1.50 -vref 0.75</pre>	Must use in case of mixed I/O voltage (V _{CCI}) design					
set_vref	Assigns a V _{REF} pin to a bank.	set_vref -bank [bankname] [pinnum] set_vref -bank Bank0 685 704 723 742 761	Must use if voltage- referenced I/Os are used					
set_vref_defaults	Sets the default V_{REF} pins for the specified bank. This command is ignored if the bank does not need a V_{REF} pin.	set_vref_defaults bankname set_vref_defaults bank2						

Table 9-3 • PDC I/O Constraints

Note: Refer to the Libero SoC User's Guide for detailed rules on PDC naming and syntax conventions.

10 – DDR for Microsemi's Low Power Flash Devices

Introduction

The I/Os in Fusion, IGLOO, and ProASIC3 devices support Double Data Rate (DDR) mode. In this mode, new data is present on every transition (or clock edge) of the clock signal. This mode doubles the data transfer rate compared with Single Data Rate (SDR) mode, where new data is present on one transition (or clock edge) of the clock signal. Low power flash devices have DDR circuitry built into the I/O tiles. I/Os are configured to be DDR receivers or transmitters by instantiating the appropriate special macros (examples shown in Figure 10-4 on page 276 and Figure 10-5 on page 277) and buffers (DDR_OUT or DDR_REG) in the RTL design. This document discusses the options the user can choose to configure the I/Os in this mode and how to instantiate them in the design.

Double Data Rate (DDR) Architecture

Low power flash devices support 350 MHz DDR inputs and outputs. In DDR mode, new data is present on every transition of the clock signal. Clock and data lines have identical bandwidths and signal integrity requirements, making them very efficient for implementing very high-speed systems. High-speed DDR interfaces can be implemented using LVDS (not applicable for IGLOO nano and ProASIC3 nano devices). In IGLOOe, ProASIC3E, AFS600, and AFS1500 devices, DDR interfaces can also be implemented using the HSTL, SSTL, and LVPECL I/O standards. The DDR feature is primarily implemented in the FPGA core periphery and is not tied to a specific I/O technology or limited to any I/O standard.



Figure 10-1 • DDR Support in Low Power Flash Devices

17 – UJTAG Applications in Microsemi's Low Power Flash Devices

Introduction

In Fusion, IGLOO, and ProASIC3 devices, there is bidirectional access from the JTAG port to the core VersaTiles during normal operation of the device (Figure 17-1). User JTAG (UJTAG) is the ability for the design to use the JTAG ports for access to the device for updates, etc. While regular JTAG is used, the UJTAG tiles, located at the southeast area of the die, are directly connected to the JTAG Test Access Port (TAP) Controller in normal operating mode. As a result, all the functional blocks of the device, such as Clock Conditioning Circuits (CCCs) with PLLs, SRAM blocks, embedded FlashROM, flash memory blocks, and I/O tiles, can be reached via the JTAG ports. The UJTAG functionality is available by instantiating the UJTAG macro directly in the source code of a design. Access to the FPGA core VersaTiles from the JTAG ports enables users to implement different applications using the TAP Controller (JTAG port). This document introduces the UJTAG tile functionality and discusses a few application examples. However, the possible applications are not limited to what is presented in this document. UJTAG can serve different purposes in many designs as an elementary or auxiliary part of the design. For detailed usage information, refer to the "Boundary Scan in Low Power Flash Devices" section on page 357.



Figure 17-1 • Block Diagram of Using UJTAG to Read FlashROM Contents

UJTAG Applications in Microsemi's Low Power Flash Devices

Typical UJTAG Applications

Bidirectional access to the JTAG port from VersaTiles—without putting the device into test mode creates flexibility to implement many different applications. This section describes a few of these. All are based on importing/exporting data through the UJTAG tiles.

Clock Conditioning Circuitry—Dynamic Reconfiguration

In low power flash devices, CCCs, which include PLLs, can be configured dynamically through either an 81-bit embedded shift register or static flash programming switches. These 81 bits control all the characteristics of the CCC: routing MUX architectures, delay values, divider values, etc. Table 17-3 lists the 81 configuration bits in the CCC.

Bit Number(s)	Control Function
80	RESET ENABLE
79	DYNCSEL
78	DYNBSEL
77	DYNASEL
<76:74>	VCOSEL [2:0]
73	STATCSEL
72	STATBSEL
71	STATASEL
<70:66>	DLYC [4:0]
<65:61>	DLYB {4:0]
<60:56>	DLYGLC [4:0]
<55:51>	DLYGLB [4:0]
<50:46>	DLYGLA [4:0]
45	XDLYSEL
<44:40>	FBDLY [4:0]
<39:38>	FBSEL
<37:35>	OCMUX [2:0]
<34:32>	OBMUX [2:0]
<31:29>	OAMUX [2:0]
<28:24>	OCDIV [4:0]
<23:19>	OBDIV [4:0]
<18:14>	OADIV [4:0]
<13:7>	FBDIV [6:0]
<6:0>	FINDIV [6:0]

Table 17-3 • Configuration Bits of Fusion, IGLOO, and ProASIC3 CCC Blocks

The embedded 81-bit shift register (for the dynamic configuration of the CCC) is accessible to the VersaTiles, which, in turn, have access to the UJTAG tiles. Therefore, the CCC configuration shift register can receive and load the new configuration data stream from JTAG.

Dynamic reconfiguration eliminates the need to reprogram the device when reconfiguration of the CCC functional blocks is needed. The CCC configuration can be modified while the device continues to operate. Employing the UJTAG core requires the user to design a module to provide the configuration data and control the CCC configuration shift register. In essence, this is a user-designed TAP Controller requiring chip resources.

Similar reconfiguration capability exists in the ProASIC^{PLUS®} family. The only difference is the number of shift register bits controlling the CCC (27 in ProASIC^{PLUS} and 81 in IGLOO, ProASIC3, and Fusion).